

ECE 8194.04 (Proposed): Group Studies:Physical Electronics of Advanced Semiconductor Devices

Course Description

Group studies in Physical Electronics of Advanced Semiconductor Devices: MOSCAPs, Gated Diode, CMOS Bulk/SOI Transistors, Photodiodes, Carrier Transport/Storage, Scaling, Mobility, CCDs, CMOS, EEPROMs, SiGe, SiC, ISFETs, BJTs, Noise and Modeling.

Prior Course Number: 894

Transcript Abbreviation: Grp Stud Adv Semi

Grading Plan: Letter Grade

Course Deliveries: Classroom

Course Levels: Graduate

Student Ranks: Masters, Doctoral

Course Offerings: Spring

Flex Scheduled Course: Never

Course Frequency: Every Year

Course Length: 14 Week

Credits: 3.0

Repeatable: No

Time Distribution: 3.0 hr Lec

Expected out-of-class hours per week: 6.0

Graded Component: Lecture

Credit by Examination: No

Admission Condition: No

Off Campus: Never

Campus Locations: Columbus

Prerequisites and Co-requisites: 5530 (730)

Exclusions: Not open to students with credit for ECE 894 (Spring 12, Class number 26147)

Cross-Listings:

Course Rationale: Train graduate students in advanced semiconductor topics.

The course is required for this unit's degrees, majors, and/or minors: No

The course is a GEC: No

The course is an elective (for this or other units) or is a service course for other units: Yes

Subject/CIP Code: 14.1001

Subsidy Level: Doctoral Course

Course Goals

Students learn about quantum effects of device scaling on performance and reliability
Students learn modeling of MOS transistors, CCDs, EEPROMs and other devices
Students learn measurement techniques for device characterization

Course Topics

Topic	Lec	Rec	Lab	Cli	IS	Sem	FE	Wor
Historical overview: MOSCAP, gated diode, high-K dielectrics, amphoteric traps	7.0							

Topic	Lec	Rec	Lab	Cli	IS	Sem	FE	Wor
Generation-recombination theory, equilibrium, non-equilibrium, steady-state and non-steady-state, conductance, surface recombination boundary conditions	4.0							
CCDs, carrier transport and operation, transfer efficiency, charge control model	4.0							
CMOS transistors (bulk, SOI, mobility, transconductance, subthreshold operation, SPICE modeling, short-channel and narrow-width effects, surface and buried channel devices, propagation delay, ion-sensitive FETs (ISFETs), hot carrier injection	7.0							
Charge pumping, interface and dielectric traps	3.0							
Physics of tunneling- floating gate and SONOS EEPROMs	4.0							
Theory of drift-field bipolar junction transistors (BJTs)	4.0							
SiGe FETs and SiC devices	3.0							
Advanced research topics (e.g. mobility, surface roughness, Coulomb scattering, noise)	3.0							

Grades

Aspect	Percent
Homework	60%
Midterm Exam	20%
Final exam	20%

Representative Textbooks and Other Course Materials

Title	Author
<i>Course notes and selected papers from the literature</i>	

ABET-EAC Criterion 3 Outcomes

Course Contribution		College Outcome
***	a	An ability to apply knowledge of mathematics, science, and engineering.
	b	An ability to design and conduct experiments, as well as to analyze and interpret data.
***	c	An ability to design a system, component, or process to meet desired needs.
	d	An ability to function on multi-disciplinary teams.
	e	An ability to identify, formulate, and solve engineering problems.
	f	An understanding of professional and ethical responsibility.
	g	An ability to communicate effectively.
	h	The broad education necessary to understand the impact of engineering solutions in a global and societal context.
	i	A recognition of the need for, and an ability to engage in life-long learning.
***	j	A knowledge of contemporary issues.
	k	An ability to use the techniques, skills, and modern engineering tools necessary for engineering practice.

Additional Notes or Comments

Being proposed for Spring 2014

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